

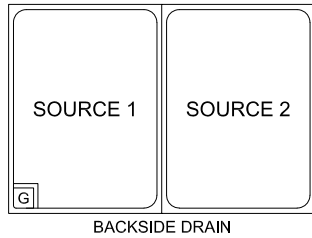
The CP802-CWDM3011P medium power P-Channel MOSFET is designed for power management and load switching applications. The 5.5 mil thick die provides an ultra low profile device that is readily attached using standard die attach wire bond processes.

APPLICATIONS:

- Load switching
- Power management
- DC-DC conversion

FEATURES:

- Low on-resistance, $r_{DS(ON)}$
- Low gate charge, Q_{gs}
- High drain current density



MECHANICAL SPECIFICATIONS:

Die Size	83.5 x 57.1 MILS
Die Thickness	5.5 MILS
Gate Bonding Pad Area	5.5 x 5.5 MILS
Source 1 Bonding Pad Area	39.1 x 54.1 MILS
Source 2 Bonding Pad Area	39.1 x 54.1 MILS
Top Side Metalization	Al-Cu - 40,000Å
Back Side Metalization	Ti/Ni/Ag - 1,000Å/3,000Å/10,000Å
Scribe Alley Width	2.36 MILS
Wafer Diameter	8 INCHES
Gross Die Per Wafer	8,360

MAXIMUM RATINGS: ($T_A=25^\circ\text{C}$)

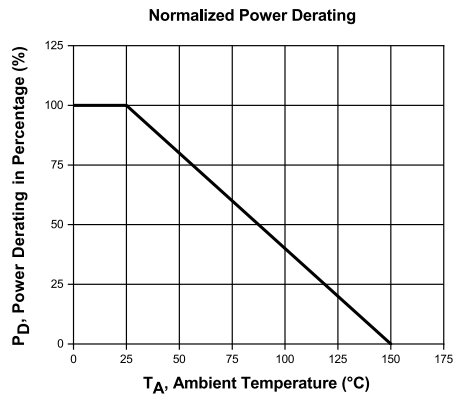
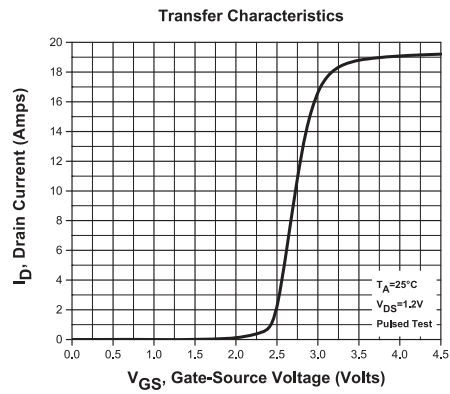
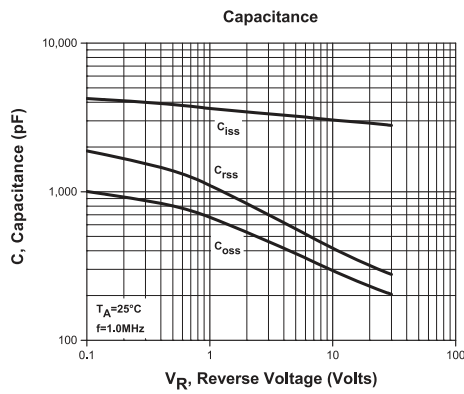
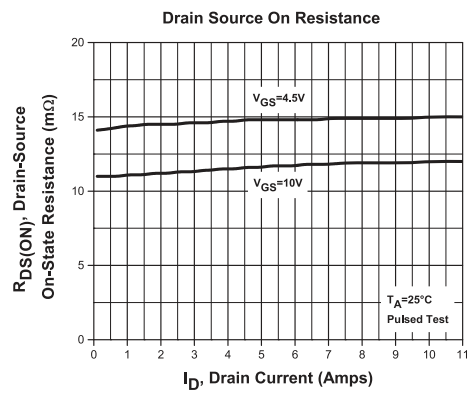
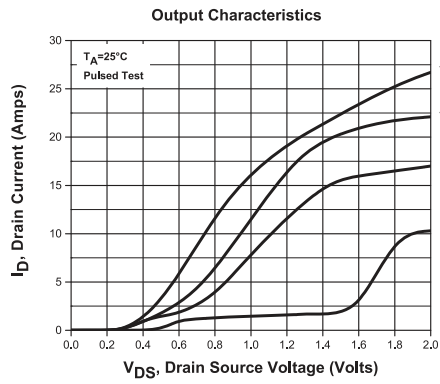
	SYMBOL		UNITS
Drain-Source Voltage	V_{DS}	30	V
Gate-Source Voltage	V_{GS}	20	V
Continuous Drain Current (Steady State)	I_D	11	A
Maximum Pulsed Drain Current, $t_p=10\mu\text{s}$	I_{DM}	50	A
Operating and Storage Junction Temperature	T_J, T_{stg}	-55 to +150	$^\circ\text{C}$

ELECTRICAL CHARACTERISTICS: ($T_A=25^\circ\text{C}$ unless otherwise noted)

SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNITS
I_{GSSF}, I_{GSSR}	$V_{GS}=20\text{V}, V_{DS}=0$			100	nA
I_{DSS}	$V_{DS}=30\text{V}, V_{GS}=0$			1.0	μA
BV_{DSS}	$V_{GS}=0, I_D=250\mu\text{A}$	30			V
$V_{GS(th)}$	$V_{GS}=V_{DS}, I_D=250\mu\text{A}$	1.0	1.4	3.0	V
V_{SD}	$V_{GS}=0, I_S=2.6\text{A}$			1.3	V
$r_{DS(ON)}$	$V_{GS}=10\text{V}, I_D=1.0\text{A}$		6.6	13	$\text{m}\Omega$
$r_{DS(ON)}$	$V_{GS}=4.5\text{V}, I_D=1.0\text{A}$		8.2	16	$\text{m}\Omega$
C_{rss}	$V_{DS}=8.0\text{V}, V_{GS}=0, f=1.0\text{MHz}$		450		pF
C_{iss}	$V_{DS}=8.0\text{V}, V_{GS}=0, f=1.0\text{MHz}$		3100		pF
C_{oss}	$V_{DS}=8.0\text{V}, V_{GS}=0, f=1.0\text{MHz}$		320		pF
$Q_{g(tot)}$	$V_{DD}=15\text{V}, V_{GS}=10\text{V}, I_D=11\text{A}$		80		nC
Q_{gs}	$V_{DD}=15\text{V}, V_{GS}=10\text{V}, I_D=11\text{A}$		7.0		nC
Q_{gd}	$V_{DD}=15\text{V}, V_{GS}=10\text{V}, I_D=11\text{A}$		10.1		nC
t_{on}	$V_{DD}=15\text{V}, V_{GS}=10\text{V}, I_D=1.0\text{A}$		49		ns
t_{off}	$R_G=6.0\Omega, R_L=15\Omega$		330		ns

CP802-CWDM3011P

Typical Electrical Characteristics



BARE DIE PACKING OPTIONS



BARE DIE IN TRAY (WAFFLE) PACK

CT: Singulated die in tray (waffle) pack.
(example: CP211-PART NUMBER-CT)

CM: Singulated die in tray (waffle) pack 100% visually inspected as per MIL-STD-750, (method 2072 transistors, method 2073 diodes).
(example: CP211-PART NUMBER-CM)



UNSAWN WAFER

WN: Full wafer, unsawn, 100% tested with reject die inked.
(example: CP211-PART NUMBER-WN)



SAWN WAFER ON PLASTIC RING

WR: Full wafer, sawn and mounted on plastic ring,
100% tested with reject die inked.
(example: CP211-PART NUMBER-WR)

Please note: Sawn Wafer on Metal Frame (WS) is possible as a special order. Please contact your Central Sales Representative at 631-435-1110.



Visit the Central website for a complete listing of specifications:
www.centrasemi.com/bdspecs

OUTSTANDING SUPPORT AND SUPERIOR SERVICES



PRODUCT SUPPORT

Central's operations team provides the highest level of support to insure product is delivered on-time.

- Supply management (Customer portals)
- Inventory bonding
- Consolidated shipping options
- Custom bar coding for shipments
- Custom product packing

DESIGNER SUPPORT/SERVICES

Central's applications engineering team is ready to discuss your design challenges. Just ask.

- Free quick ship samples (2nd day air)
- Online technical data and parametric search
- SPICE models
- Custom electrical curves
- Environmental regulation compliance
- Customer specific screening
- Up-screening capabilities
- Special wafer diffusions
- PbSn plating options
- Package details
- Application notes
- Application and design sample kits
- Custom product and package development

REQUESTING PRODUCT PLATING

1. If requesting Tin/Lead plated devices, add the suffix "TIN/LEAD" to the part number when ordering (example: 2N2222A TIN/LEAD).
2. If requesting Lead (Pb) Free plated devices, add the suffix "PBFREE" to the part number when ordering (example: 2N2222A PBFREE).

CONTACT US

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